



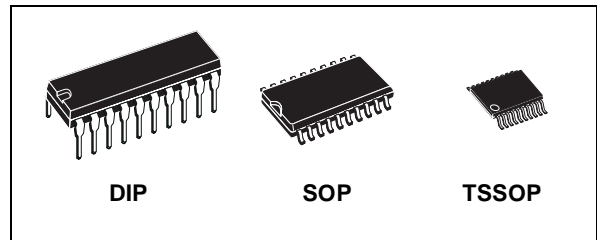
# M74HCT245

## OCTAL BUS TRANSCEIVER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED:  
 $t_{PD} = 13ns$  (TYP.) at  $V_{CC} = 4.5V$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu A$  (MAX.) at  $T_A = 25^\circ C$
- COMPATIBLE WITH TTL OUTPUTS :  
 $V_{IH} = 2V$  (MIN.)  $V_{IL} = 0.8V$  (MAX)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 6mA$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \cong t_{PHL}$
- PIN AND FUNCTION COMPATIBLE WITH  
74 SERIES 245

### DESCRIPTION

The M74HCT245 is an advanced high-speed CMOS OCTAL BUS TRANSCEIVER (3-STATE) fabricated with silicon gate C<sup>2</sup>MOS technology. This IC is intended for two-way asynchronous communication between data buses, and the direction of data transmission is determined by DIR input. The enable input  $\bar{G}$  can be used to disable the device so that the buses are effectively isolated.

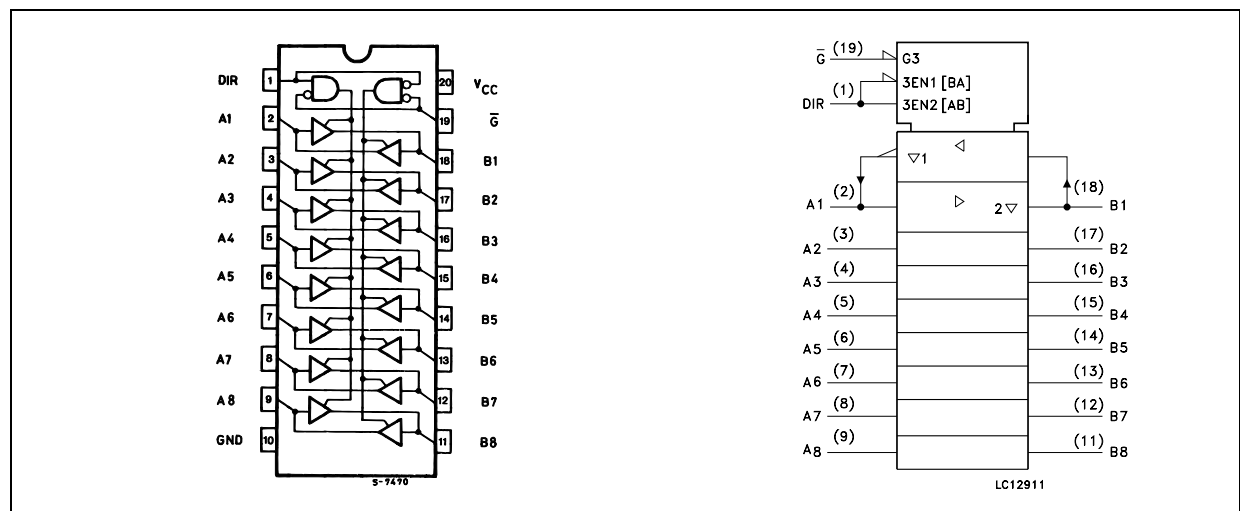


### ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT245B1R	
SOP	M74HCT245M1R	M74HCT245RM13TR
TSSOP		M74HCT245TTR

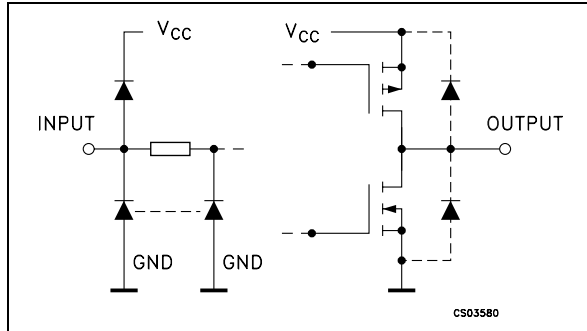
All inputs are equipped with protection circuits against static discharge and transient excess voltage.  
All floating bus terminals during High Z State must be held HIGH or LOW.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



## M74HCT245

### INPUT AND OUTPUT EQUIVALENT CIRCUIT



### PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	DIR	Directional Control
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs/Outputs
18, 17, 16, 15, 14, 13, 12, 11	B1 to B8	Data Inputs/Outputs
19	G	Output Enable Input
10	GND	Ground (0V)
20	V <sub>CC</sub>	Positive Supply Voltage

### TRUTH TABLE

INPUTS		FUNCTION		OUTPUT
$\overline{G}$	DIR	A BUS	B BUS	Y <sub>n</sub>
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	Z	Z	Z

X : Don't Care  
Z : High Impedance

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 35	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 70	mA
P <sub>D</sub>	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (V <sub>CC</sub> = 4.5 to 5.5V)	0 to 500	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
V <sub>IL</sub>	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V <sub>OH</sub>	High Level Output Voltage	4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		V
			I <sub>O</sub> =-6.0 mA	4.18	4.31		4.13		4.10		
V <sub>OL</sub>	Low Level Output Voltage	4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
			I <sub>O</sub> =6.0 mA		0.17	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			± 0.5		± 5		± 10	μA
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			4		40		80	μA
Δ I <sub>CC</sub>	Additional Worst Case Supply Current	5.5	Per Input pin V <sub>I</sub> = 0.5V or V <sub>I</sub> = 2.4V Other Inputs at V <sub>CC</sub> or GND I <sub>O</sub> = 0			2.0		2.9		3.0	mA

AC ELECTRICAL CHARACTERISTICS (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6ns)

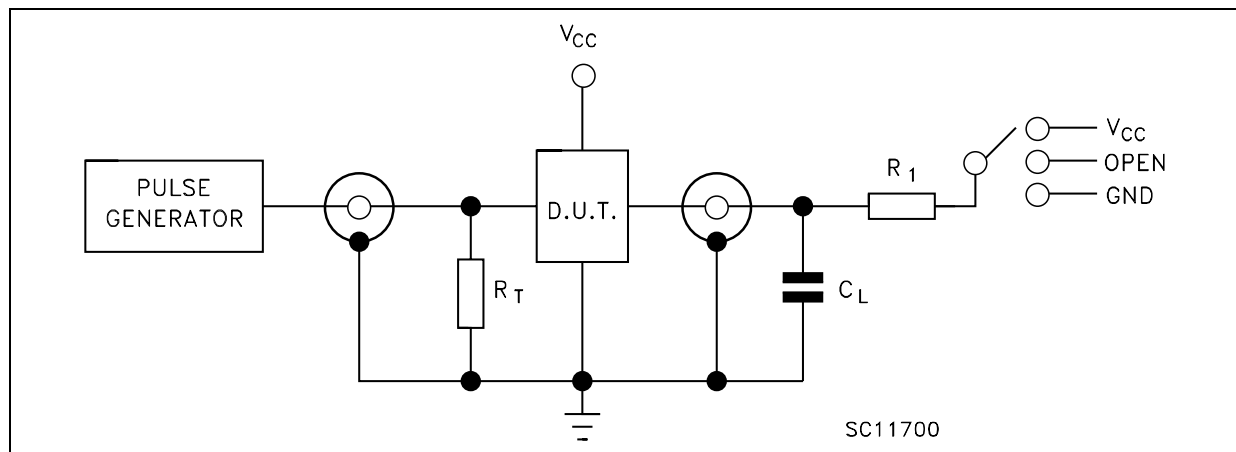
Symbol	Parameter	Test Condition			Value							Unit
		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t <sub>TLH</sub> t <sub>THL</sub>	Output Transition Time	4.5	50			7	12		15		18	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	4.5	50			13	22		28		33	ns
			150			18	30		38		45	
t <sub>PZL</sub> t <sub>PZH</sub>	High Impedance Output Enable Time	4.5	50	R <sub>L</sub> = 1 KΩ		19	30		38		45	ns
			150	R <sub>L</sub> = 1 KΩ		24	38		48		57	
t <sub>PLZ</sub> t <sub>PHZ</sub>	High Impedance Output Disable Time	4.5	50	R <sub>L</sub> = 1 KΩ		17	30		38		45	ns

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value							Unit
		V <sub>CC</sub> (V)			T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			DIR, $\overline{G}$		5	10		10		10	pF
C <sub>I/OUT</sub>	Output Capacitance			An, Bn		13						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)					41						pF

1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$  (per circuit)

## TEST CIRCUIT

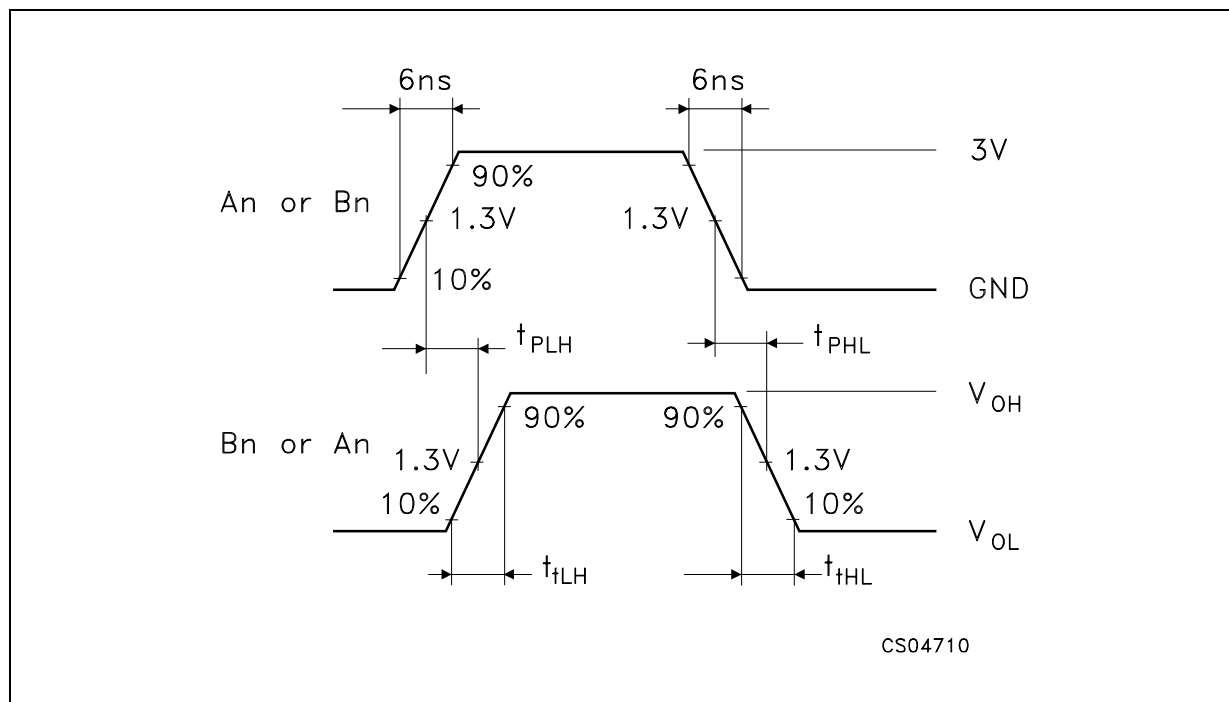
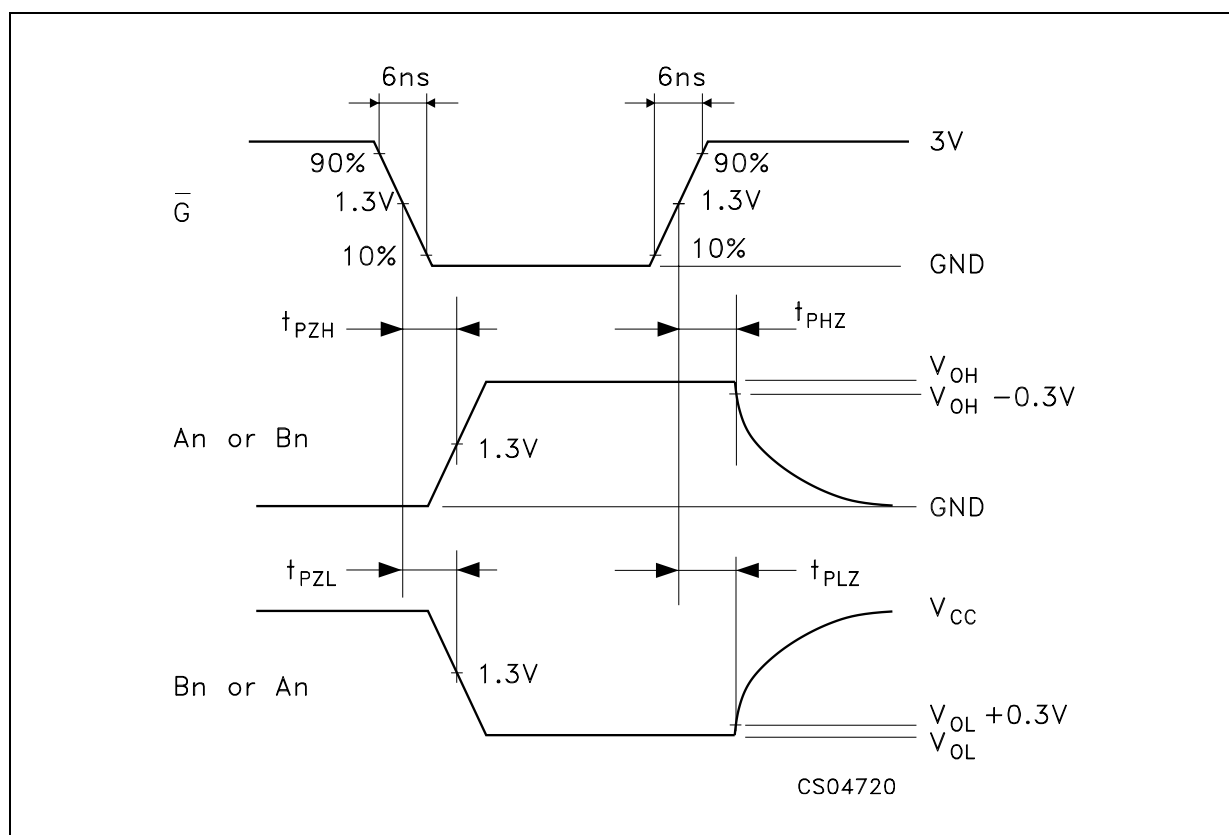


TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	V <sub>CC</sub>
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

C<sub>L</sub> = 50pF/150pF or equivalent (includes jig and probe capacitance)

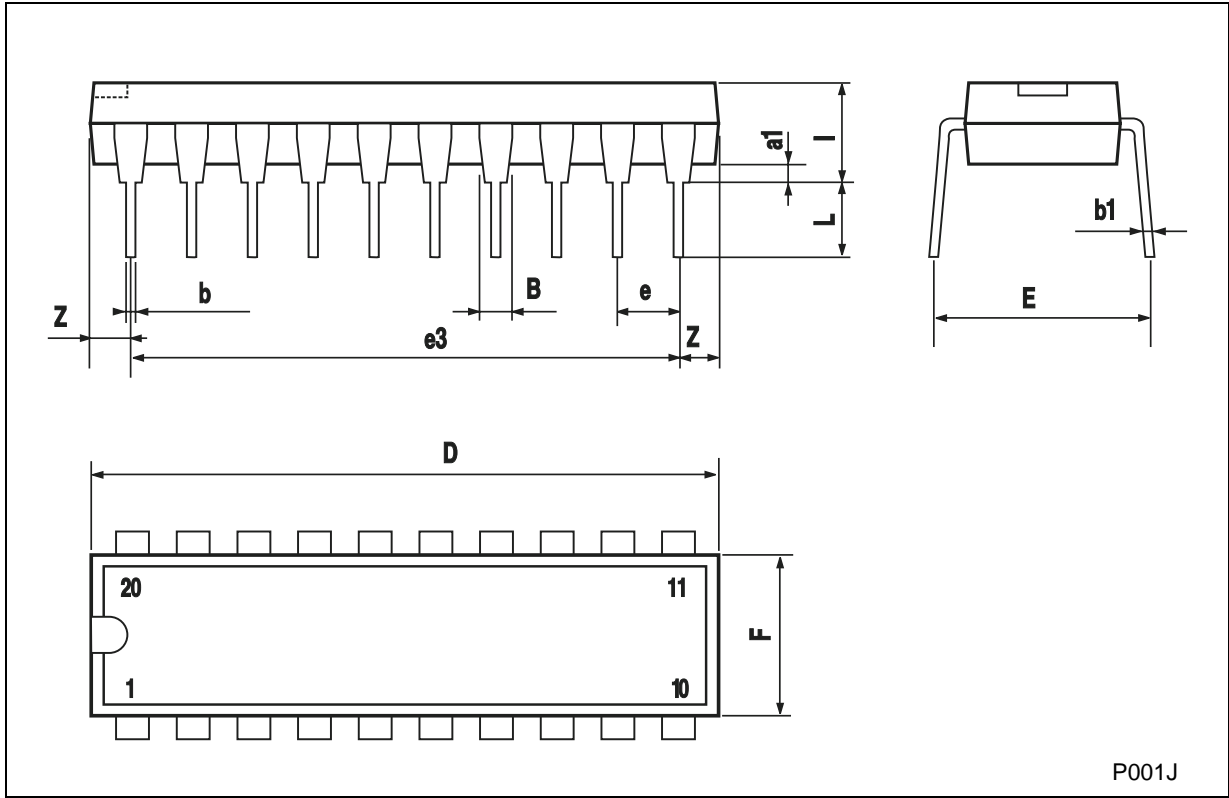
R<sub>1</sub> = 1KΩ or equivalent

R<sub>T</sub> = Z<sub>OUT</sub> of pulse generator (typically 50Ω)

**WAVEFORM 1 : PROPAGATION DELAY TIME** ( $f=1\text{MHz}$ ; 50% duty cycle)**WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIME** ( $f=1\text{MHz}$ ; 50% duty cycle)

Plastic DIP-20 (0.25) MECHANICAL DATA

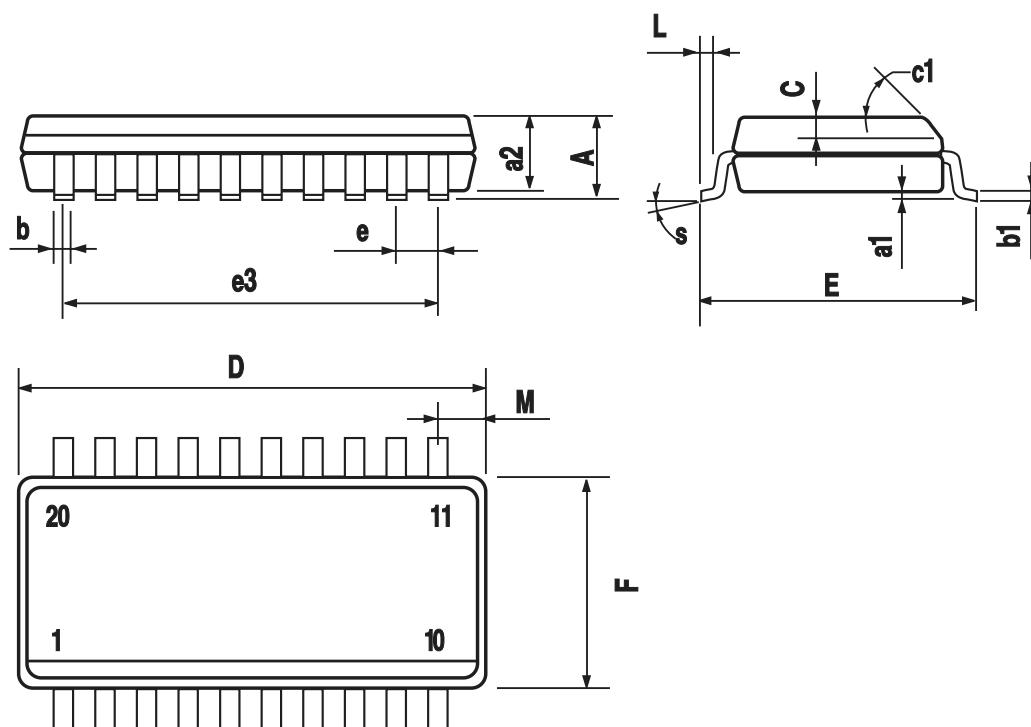
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



P001J

## SO-20 MECHANICAL DATA

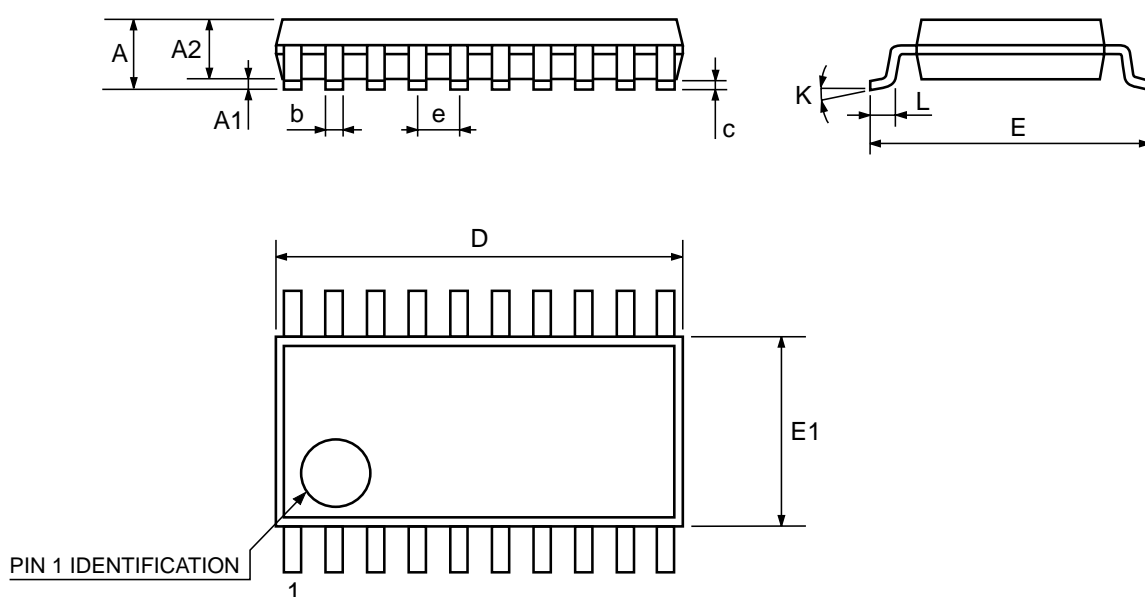
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



PO13L

## TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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